

Q1 microelectronic element using a second fusible material, the second fusible material having a second melting temperature that is lower than the first melting temperature of the first fusible material. During the electrically interconnecting step, the second fusible material is maintained at a temperature that is greater than or equal to the second melting temperature and less than the first melting temperature of the first fusible material. The method also includes testing the microelectronic assembly after the electrically interconnecting step while maintaining the second fusible material at a temperature that is greater than or equal to the second melting temperature.

IN THE CLAIMS

1. (Amended) A method of making a microelectronic assembly comprising:

Q2 providing a first microelectronic element having one or more conductive bumps, said conductive bumps including a first fusible material that transforms from a solid to a liquid at a first melting temperature;

providing a second microelectronic element having one or more conductive elements;

electrically interconnecting said conductive bumps of said first microelectronic element and said conductive elements of said second microelectronic element using a second fusible material, said second fusible material having a second melting temperature that is lower than the first melting temperature of said first fusible material;

during the electrically interconnecting step, maintaining said second fusible material at a temperature that is greater than or equal to the second melting temperature and

Q2 less than the first melting temperature of said first fusible material; and

testing said microelectronic assembly after the electrically interconnecting step while maintaining said second fusible material at a temperature that is greater than or equal to the second melting temperature.

Q3 5. (Amended) The method as claimed in claim 1, further comprising lowering the temperature of said second fusible material to a temperature that is less than the second melting temperature.

Q4 8. (Amended) The method as claimed in claim 1, further comprising after the testing step, raising the temperature of the first fusible material to a temperature that is greater than the first melting temperature of said first fusible material for mixing the first and second fusible materials together to form one or more conductive masses.

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